

What is claimed is:

1. A plasma display panel, comprising:
a first substrate;
a second substrate facing the first substrate with a discharge space therebetween;
a sealing layer located between the first substrate and the second substrate; and
a buffer layer formed between the first substrate and the sealing layer to compensate the thermal stress of the first substrate and the sealing layer.
2. The plasma display panel according to claim 1, wherein the buffer layer is composed of PbO of 45~55%, B₂O₃ of 10~20%, Al₂O₃ of 10~20% and SiO₂ of 15~25%.
3. The plasma display panel according to claim 1, wherein the thermal expansion coefficient of the buffer layer is different from the thermal expansion coefficient of the first substrate.
4. The plasma display panel according to claim 1, wherein the thermal expansion coefficient of the buffer layer is the same as the thermal expansion coefficient of the first substrate.
5. The plasma display panel according to claim 1, wherein the thermal expansion coefficient of the buffer layer is different from the thermal expansion coefficient of the sealing layer.
6. The plasma display panel according to claim 1, wherein the thermal expansion coefficient of the buffer layer is the same

as the thermal expansion coefficient of the sealing layer.

7. The plasma display panel according to claim 1, wherein the thermal expansion coefficient of the first substrate is around $80 \times 10^{-7} \sim 95 \times 10^{-7} / ^\circ\text{C}$.

8. The plasma display panel according to claim 1, wherein the thermal expansion coefficient of the sealing layer is around $65 \times 10^{-7} \sim 80 \times 10^{-7} / ^\circ\text{C}$.

9. The plasma display panel according to claim 1, wherein the thermal expansion coefficient of the buffer layer is around $72 \times 10^{-7} \sim 86 \times 10^{-7} / ^\circ\text{C}$.

10. The plasma display panel according to claim 1, further comprising:

a protective film formed on the first substrate where the buffer layer has been formed.

11. The plasma display panel according to claim 1, further comprising:

an upper dielectric layer formed on the first substrate; and
a protective film formed on the upper dielectric layer.

12. The plasma display panel according to claim 11, wherein the buffer layer is formed to be extended from the upper dielectric layer.

13. The plasma display panel according to claim 12, wherein the buffer layer is separately formed of a different material from

the upper dielectric layer.

14. The plasma display panel according to claim 12, wherein the buffer layer is formed of the same material as the upper dielectric layer.

15. A fabricating method of a plasma display panel, comprising the steps of:

forming a buffer layer on a first substrate; and

forming a sealing layer on the buffer layer.

16. The fabricating method according to claim 15, further comprising the steps of:

providing a second substrate facing the first substrate where the sealing layer has been formed; and

joining the first substrate with the second substrate.

17. The fabricating method according to claim 15, further comprising the steps of:

forming an upper dielectric layer on the first substrate;

and

forming a protective film on the upper dielectric layer.

18. The fabricating method according to claim 15, wherein the buffer layer is composed of PbO of 45~55%, B₂O₃ of 10~20%, Al₂O₃ of 10~20% and SiO₂ of 15~25%.

19. The fabricating method according to claim 15, wherein the thermal expansion coefficient of the buffer layer is different from the thermal expansion coefficient of the first substrate.

20. The fabricating method according to claim 15, wherein the thermal expansion coefficient of the buffer layer is the same as the thermal expansion coefficient of the first substrate.

21. The fabricating method according to claim 15, wherein the thermal expansion coefficient of the buffer layer is different from the thermal expansion coefficient of the sealing layer.

22. The fabricating method according to claim 15, wherein the thermal expansion coefficient of the buffer layer is the same as the thermal expansion coefficient of the sealing layer.

23. The fabricating method according to claim 15, wherein the thermal expansion coefficient of the first substrate is around $80 \times 10^{-7} \sim 95 \times 10^{-7} / ^\circ\text{C}$.

24. The fabricating method according to claim 15, wherein the thermal expansion coefficient of the sealing layer is around $65 \times 10^{-7} \sim 80 \times 10^{-7} / ^\circ\text{C}$.

25. The fabricating method according to claim 15, wherein the thermal expansion coefficient of the buffer layer is around $72 \times 10^{-7} \sim 86 \times 10^{-7} / ^\circ\text{C}$.